

BAW56/BAV70/BAV99

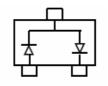
SWITCHING DIODE

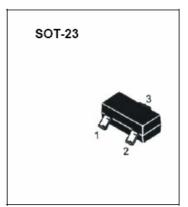
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance









BAW56 Marking: A1

BAV70 Marking: A4

BAV99 Marking: A7

Maximum Ratings @T_A=25℃

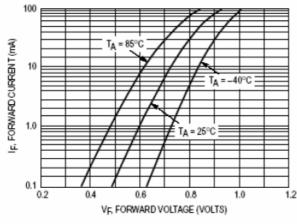
Parameter	Symbol	Limits	Unit
Reverse voltage	V _R	70	٧
Forward Current	I _F	200	mA
Peak Forward Surge Current	I _{FM(surge)}	500	mA
Power Dissipation	P₀	225	mW
Thermal Resistance Junction to Ambient Air	R _{eJA}	556	°C/W
Junction temperature	TJ	150	℃
Storage temperature range	T _{STG}	-55-150	℃

Electrical Characteristics @T_A=25℃

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _R	70			٧	I _R =100μA
Forward voltage	V _{F1}			0.715	٧	I _F =1mA
	V _{F2}			0.855	٧	I _F =10mA
	V _{F3}			1	٧	I _F =50mA
	V _{F4}			1.25	٧	I _F =150mA
Reverse current	I _R			2.5	μΑ	V _R =70V
Capacitance between terminals	Ст			1.5	pF	V _R =0,f=1MHz
Reverse recovery time	trr			6	ns	I _F = I _R = 10mA,
						Irr= 0.1 x I _R , R _L = 100Ω

Typical Characteristics

BAW56/BAV70/BAV99





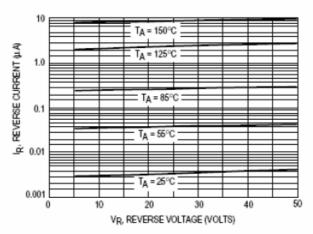


Figure 2 Leakage Current

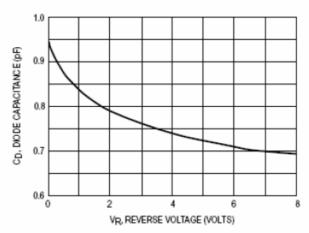


Figure 3 Capacitance